
2SJ160, 2SJ161, 2SJ162

Silicon P-Channel MOS FET

HITACHI

Application

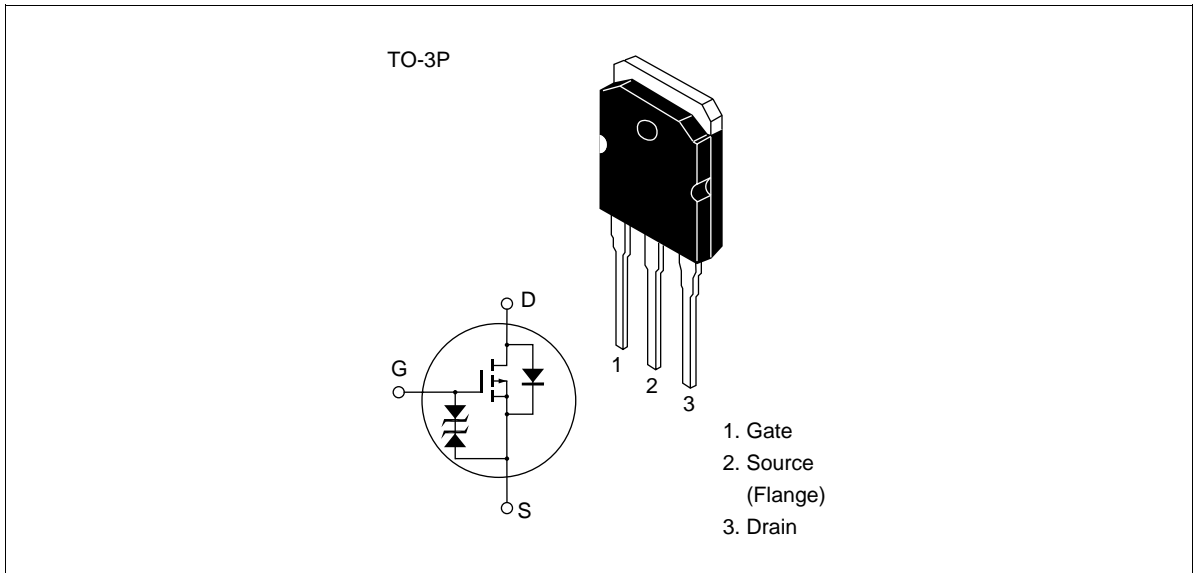
Low frequency power amplifier

Complementary pair with 2SK1056, 2SK1057 and 2SK1058

Features

- Good frequency characteristic
- High speed switching
- Wide area of safe operation
- Enhancement-mode
- Good complementary characteristics
- Equipped with gate protection diodes
- Suitable for audio power amplifier

Outline



Absolute Maximum Ratings (Ta = 25°C)

Item		Symbol	Ratings	Unit
Drain to source voltage	2SJ160	V_{DSX}	-120	V
	2SJ161		-140	
	2SJ162		-160	
Gate to source voltage		V_{GSS}	±15	V
Drain current		I_D	-7	A
Body to drain diode reverse drain current		I_{DR}	-7	A
Channel dissipation		P_{ch}^{*1}	100	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	-55 to +150	°C

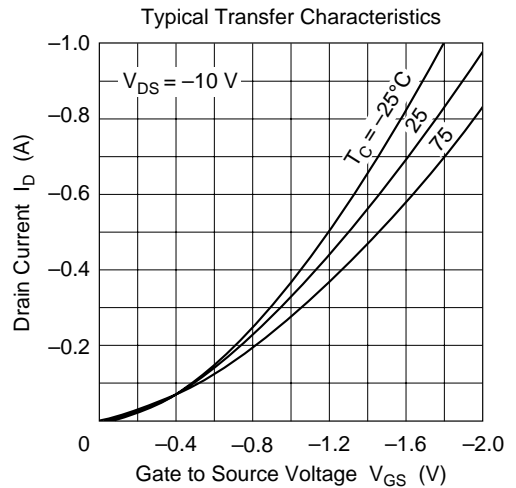
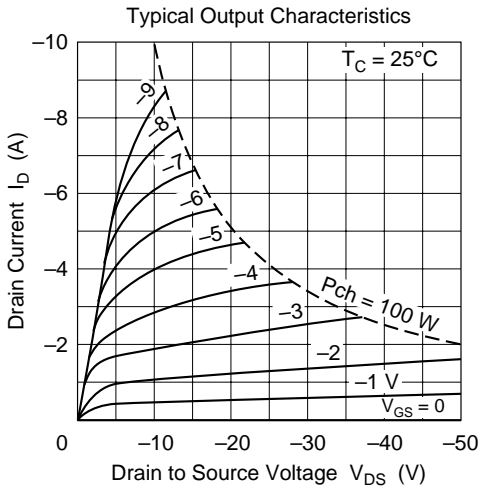
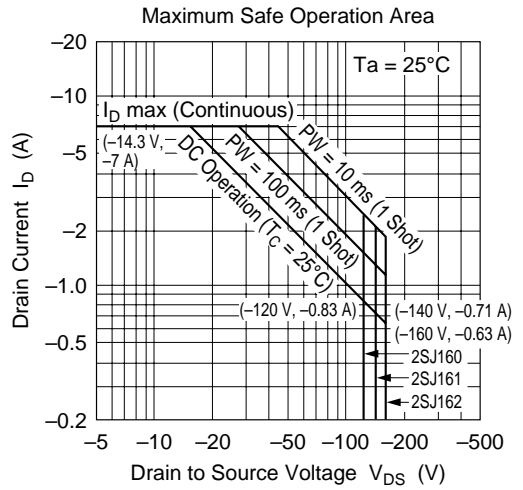
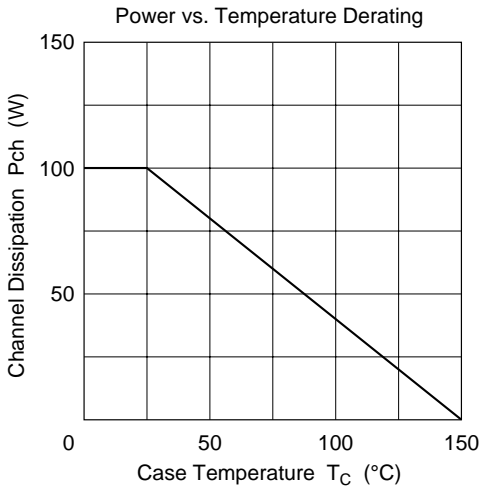
Note: 1. Value at $T_c = 25^\circ\text{C}$

Electrical Characteristics (Ta = 25°C)

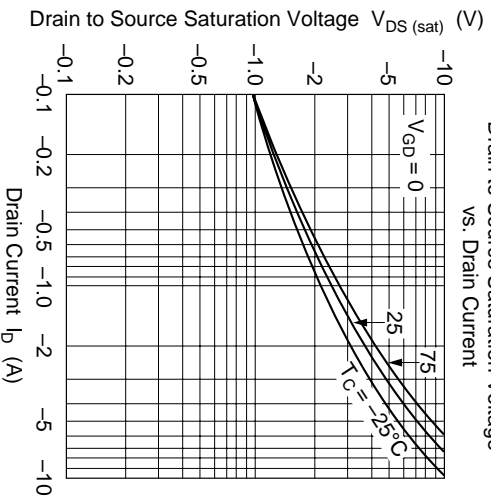
Item		Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	2SJ160	$V_{(BR)DSX}$	-120	—	—	V	$I_D = -10 \text{ mA}, V_{GS} = 10 \text{ V}$
	2SJ161		-140	—	—	V	
	2SJ162		-160	—	—	V	
Gate to source breakdown voltage		$V_{(BR)GSS}$	± 15	—	—	V	$I_G = \pm 100 \mu\text{A}, V_{DS} = 0$
Gate to source cutoff voltage		$V_{GS(off)}$	-0.15	—	-1.45	V	$I_D = -100 \text{ mA}, V_{DS} = -10 \text{ V}$
Drain to source saturation voltage		$V_{DS(sat)}$	—	—	-12	V	$I_D = -7 \text{ A}, V_{GD} = 0^{*1}$
Forward transfer admittance		$ y_{fs} $	0.7	1.0	1.4	S	$I_D = -3 \text{ A}, V_{DS} = -10 \text{ V}^{*1}$
Input capacitance		C_{iss}	—	900	—	pF	$V_{GS} = 5 \text{ V}, V_{DS} = -10 \text{ V},$
Output capacitance		C_{oss}	—	400	—	pF	$f = 1 \text{ MHz}$
Reverse transfer capacitance		C_{rss}	—	40	—	pF	
Turn-on time		t_{on}	—	230	—	ns	$V_{DD} = -20 \text{ V}, I_D = -4 \text{ A}$
Turn-off time		t_{off}	—	110	—	ns	

Note: 1. Pulse test

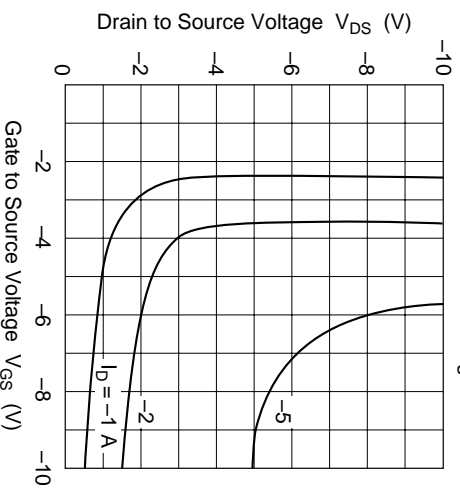
2SJ160, 2SJ161, 2SJ162



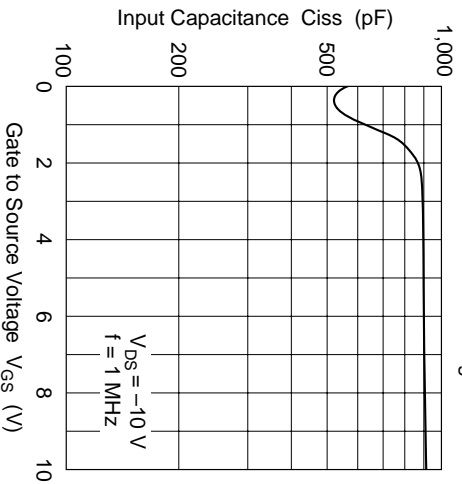
Drain to Source Saturation Voltage $V_{DS(sat)}$ vs. Drain Current



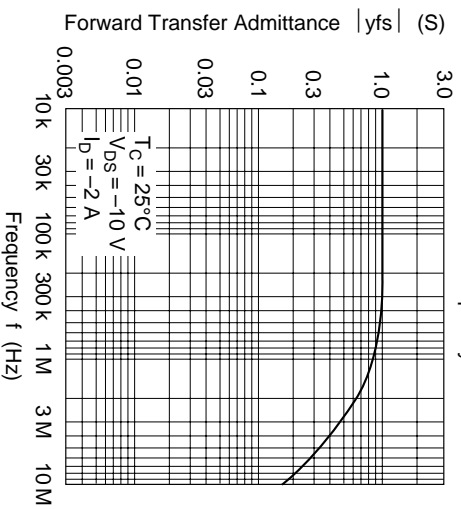
Drain to Source Voltage V_{DS} vs. Gate to Source Voltage V_{GS}

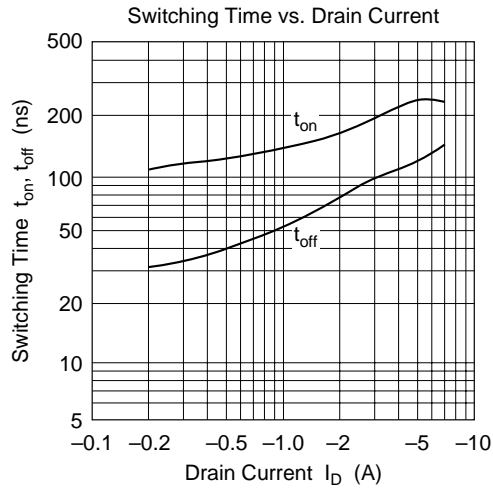


Input Capacitance vs. Gate to Source Voltage

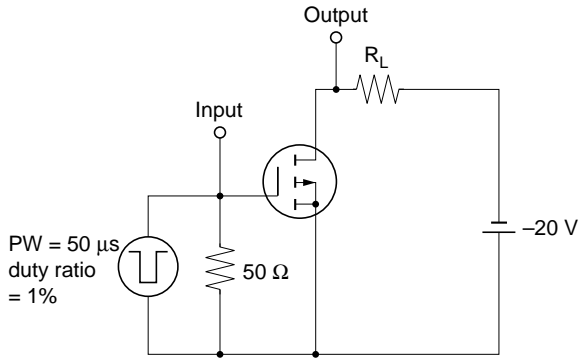


Forward Transfer Admittance vs. Frequency

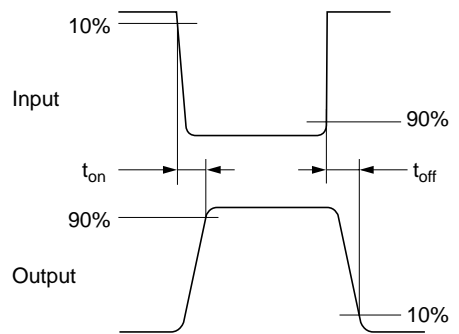


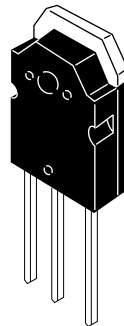
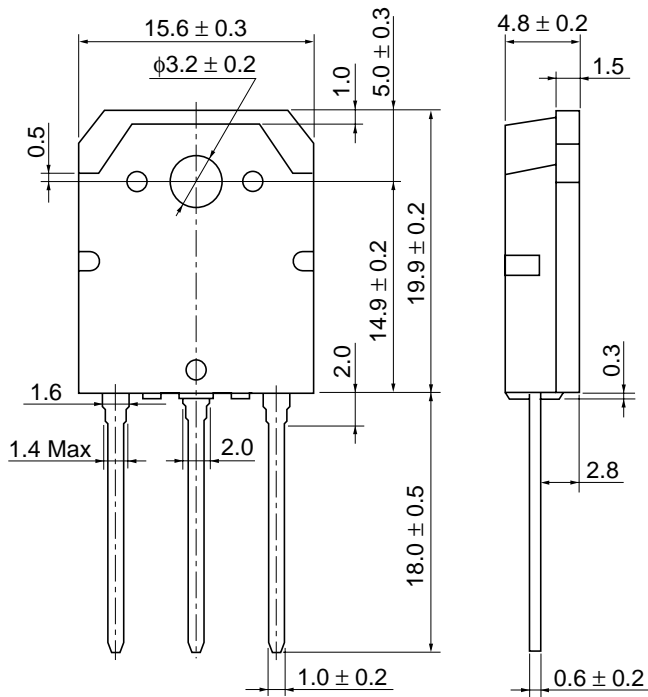


Switching Time Test Circuit



Waveforms





Hitachi Code	TO-3P
JEDEC	—
EIAJ	Conforms
Weight (reference value)	5.0 g

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